### THERMAL CHARACTERISTICS

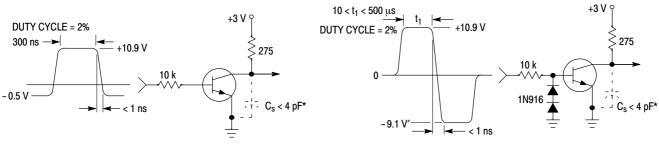
Characteristic (One Junction Heated)	Symbol	Мах	Unit	
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C (Note 1)	PD	357 2.9	mW mW/°C	
Thermal Resistance Junction-to-Ambient (Note 1)	R <sub>0JA</sub>	350	°C/W	
Characteristic (Both Junctions Heated)	Symbol	Max	Unit	
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$ (Note 1)	PD	500 4.0	mW mW/°C	
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{ hetaJA}$	250	°C/W	
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C	

1. FR-4 @ Minimum Pad

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS		•		•
Collector – Emitter Breakdown Voltage (Note 2) ( $I_C = 1.0 \text{ mAdc}, I_B = 0$ )	V <sub>(BR)CEO</sub>	40	-	Vdc
Collector – Base Breakdown Voltage ( $I_C = 10 \ \mu Adc$ , $I_E = 0$ )	V <sub>(BR)CBO</sub>	60	-	Vdc
Emitter – Base Breakdown Voltage (I <sub>E</sub> = 10 $\mu$ Adc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	6.0	-	Vdc
Base Cutoff Current (V <sub>CE</sub> = 30 Vdc, V <sub>EB</sub> = 3.0 Vdc)	I <sub>BL</sub>	-	50	nAdc
Collector Cutoff Current (V <sub>CE</sub> = 30 Vdc, V <sub>EB</sub> = 3.0 Vdc)	I <sub>CEX</sub>	-	50	nAdc
ON CHARACTERISTICS (Note 2)				
$ \begin{array}{l} \text{DC Current Gain} \\ (I_{C} = 0.1 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}) \\ (I_{C} = 1.0 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}) \\ (I_{C} = 10 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}) \\ (I_{C} = 50 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}) \\ (I_{C} = 100 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}) \\ (I_{C} = 100 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}) \end{array} $	h <sub>FE</sub>	40 70 100 60 30	- - 300 - -	-
Collector – Emitter Saturation Voltage ( $I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc}$ ) ( $I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc}$ )	V <sub>CE(sat)</sub>		0.2 0.3	Vdc
Base – Emitter Saturation Voltage $(I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc})$ $(I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc})$	V <sub>BE(sat)</sub>	0.65 -	0.85 0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS		•		
Current-Gain – Bandwidth Product ( $I_C$ = 10 mAdc, $V_{CE}$ = 20 Vdc, f = 100 MHz)	f <sub>T</sub>	300	-	MHz
Output Capacitance (V <sub>CB</sub> = 5.0 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	-	4.0	pF
Input Capacitance (V <sub>EB</sub> = 0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>ibo</sub>	-	8.0	pF
Input Impedance (V <sub>CE</sub> = 10 Vdc, $I_C$ = 1.0 mAdc, f = 1.0 kHz)	h <sub>ie</sub>	1.0 2.0	10 12	kΩ
Voltage Feedback Ratio (V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 1.0 mAdc, f = 1.0 kHz)	h <sub>re</sub>	0.5 0.1	8.0 10	X 10-4
Small-Signal Current Gain (V <sub>CE</sub> = 10 Vdc, $I_C$ = 1.0 mAdc, f = 1.0 kHz)	h <sub>fe</sub>	100 100	400 400	-
Output Admittance ( $V_{CE}$ = 10 Vdc, $I_C$ = 1.0 mAdc, f = 1.0 kHz)	h <sub>oe</sub>	1.0 3.0	40 60	μmhos
Noise Figure (V <sub>CE</sub> = 5.0 Vdc, I <sub>C</sub> = 100 $\mu$ Adc, R <sub>S</sub> = 1.0 k $\Omega$ , f = 1.0 kHz)	NF		5.0 4.0	dB

SWITCHING CHARACTERISTICS						
Delay Time	$(V_{CC} = 3.0 \text{ Vdc}, V_{BE} = -0.5 \text{ Vdc})$	t <sub>d</sub>	-	35		
Rise Time	$(I_{\rm C} = 10 \text{ mAdc}, I_{\rm B1} = 1.0 \text{ mAdc})$	tr	-	35		
Storage Time	$(V_{CC} = 3.0 \text{ Vdc}, I_C = 10 \text{ mAdc})$	t <sub>s</sub>	-	200		
Fall Time	(I <sub>B1</sub> = I <sub>B2</sub> = 1.0 mAdc)	t <sub>f</sub>	-	50		

2. Pulse Test: Pulse Width  $\leq$  300 µs; Duty Cycle  $\leq$  2.0%.



\* Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time Equivalent Test Circuit

Figure 2. Storage and Fall Time Equivalent Test Circuit

ns

ns

### **TYPICAL TRANSIENT CHARACTERISTICS**

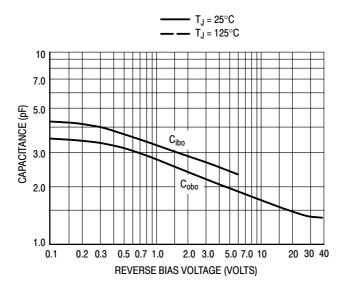
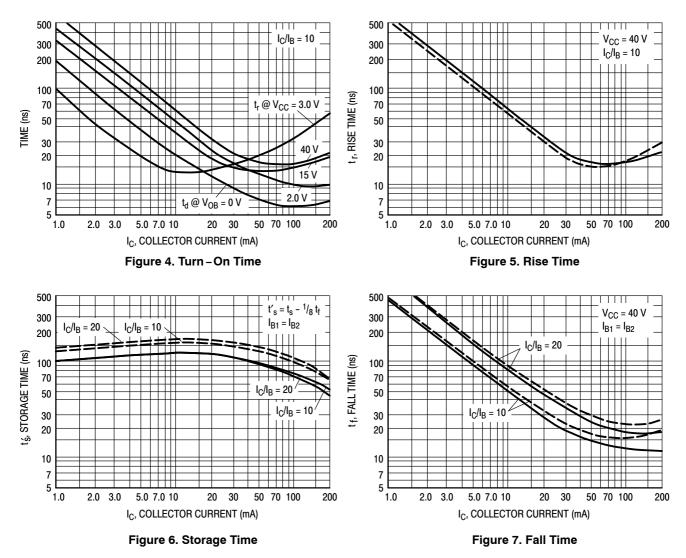


Figure 3. Capacitance



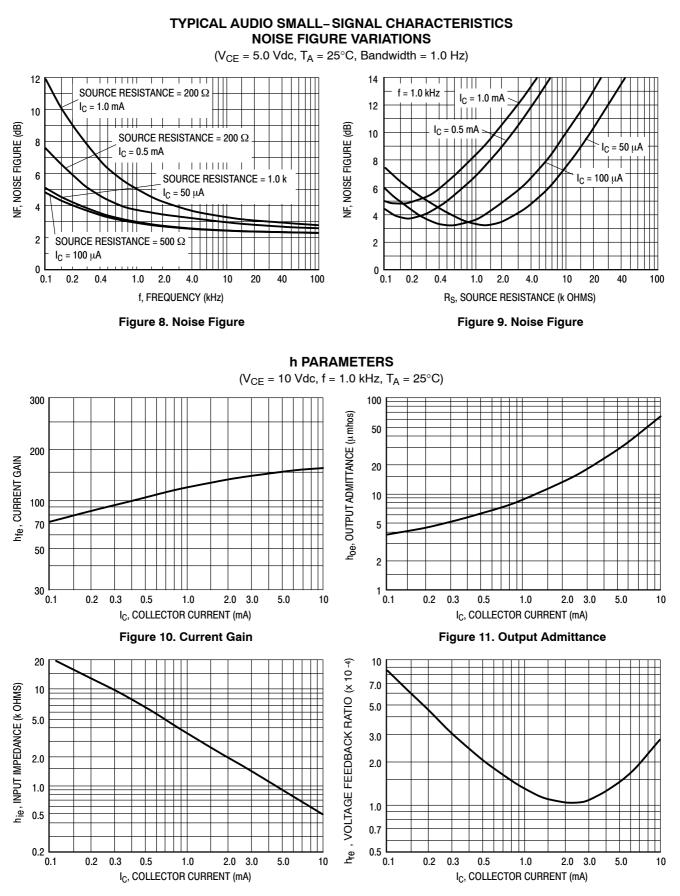
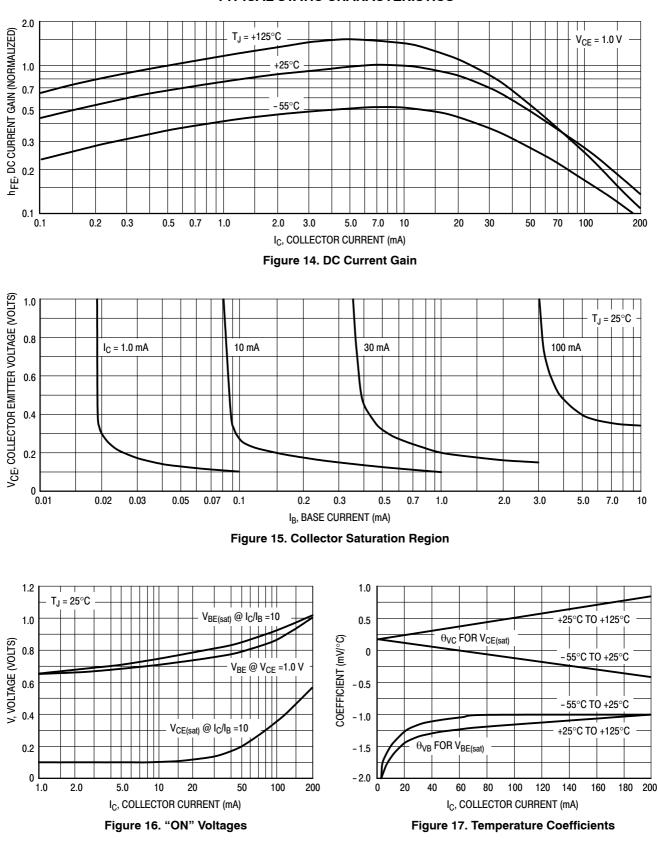


Figure 12. Input Impedance

Figure 13. Voltage Feedback Ratio



### **TYPICAL STATIC CHARACTERISTICS**

#### PACKAGE DIMENSIONS

SOT-563, 6 LEAD CASE 463A-01

ISSUE F

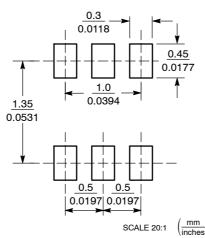
D -X-È  $H_{F}$ <u>-</u>Y 2 3 b 6 PL C е  $\oplus$ 0.08 (0.003) M X Y

NOTES 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETERS

3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.50	0.55	0.60	0.020	0.021	0.023	
b	0.17	0.22	0.27	0.007	0.009	0.011	
С	0.08	0.12	0.18	0.003	0.005	0.007	
D	1.50	1.60	1.70	0.059	0.062	0.066	
Е	1.10	1.20	1.30	0.043	0.047	0.051	
е		0.5 BSC			0.02 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012	
HE	1.50	1.60	1.70	0.059	0.062	0.066	

#### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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